In the Abstract

Please amend the abstract as follows:

A semiconductor laser device having a waveguide constructed in a stack of layers including, on a substrate [[(101)]] transparent and having a refractive index n_s for laser light, a first clad layer [[(103)]] of a refractive index n_{cl}, a second clad layer [[(104)]] of a refractive index n_{c2}, a third clad layer [[(105)]] of a refractive index n_{c3}, a first conductivity type guide layer [[(105)]] of a refractive index n_g, an active quantum well layer [[(107)]], a second conductivity type guide layer [[(109)]], a second conductivity type clad layer [[(110)]], and a second conductivity type contact layer [(111)]] deposited in this order, wherein the waveguide has an effective refractive index n_e, and a relationship of $n_{c2} < (n_{c1}, n_{c3}) < n_e < (n_s, n_g)$ is satisfied.